

Silicon NPN Power Transistors

2SD1632

DESCRIPTION

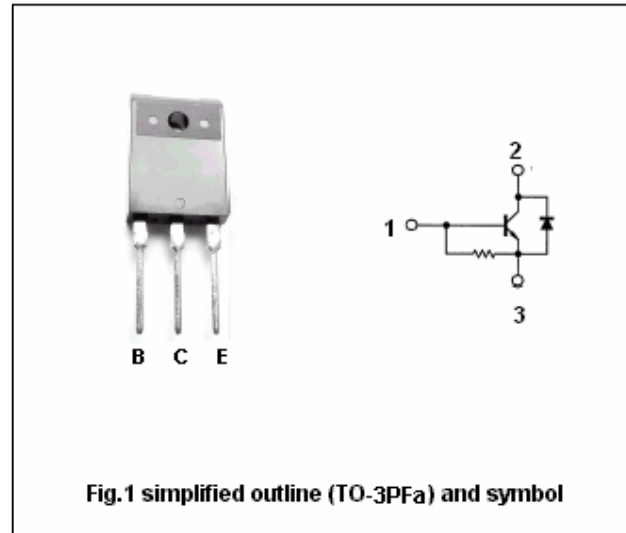
- With TO-3PFa package
- High voltage ,high speed
- Built-in damper diode
- Wide area of safe operation

APPLICATIONS

- For horizontal deflection output applications

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |

Absolute maximum ratings($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------|-----------------------------|----------------|---------|------|
| V_{CBO} | Collector-base voltage | Open emitter | 1500 | V |
| V_{EBO} | Emitter-base voltage | Open collector | 5 | V |
| I_C | Collector current | | 4 | A |
| I_{CM} | Collector current-peak | | 15 | A |
| I_{BM} | Base current | | 3.5 | A |
| P_C | Collector power dissipation | $T_C=25$ | 70 | W |
| T_j | Junction temperature | | 130 | |
| T_{stg} | Storage temperature | | -55~130 | |

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CHARACTERISTICS

Tj=25 unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------|--------------------------------------|--|-----|------|-----|---------|
| $V_{(BR)EBO}$ | Emitter-base breakdown voltage | $I_E=500mA ; I_C=0$ | 5 | | | V |
| V_{CEsat} | Collector-emitter saturation voltage | $I_C=3A ; I_B=1A$ | | | 1.0 | V |
| V_{BEsat} | Base-emitter saturation voltage | $I_C=3A ; I_B=1A$ | | | 1.5 | V |
| I_{CBO} | Collector cut-off current | $V_{CB}=750V ; I_E=0$ | | | 50 | μA |
| | | $V_{CB}=1500V ; I_E=0$ | | | 1 | mA |
| h_{FE} | DC current gain | $I_C=3A ; V_{CE}=10V$ | 5 | | 15 | |
| V_F | Diode forward voltage | $I_C=-4A$ | | | 2.2 | V |
| Switching times | | | | | | |
| t_{stg} | Storage time | $I_C=3A$ $I_{Bend}=1A ; I_{Leak}=5 \mu H$ | 4 | | 9 | μs |
| t_f | Fall time | | | | 0.8 | μs |

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PACKAGE OUTLINE

